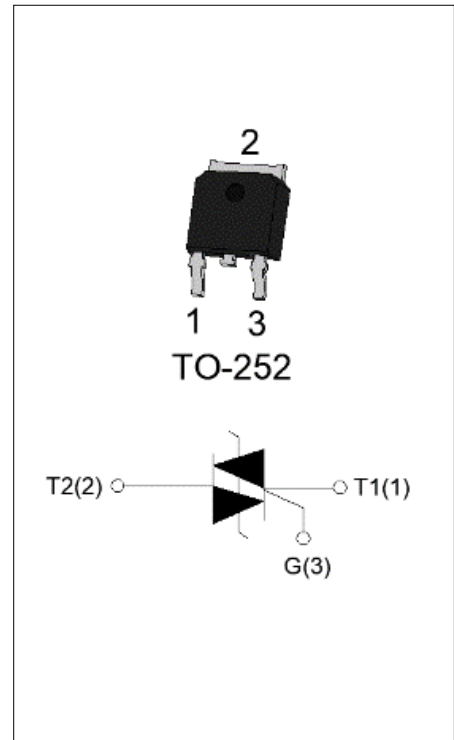




ACJT210-8K 2A TRIAC

Rev.A.1.0

The ACJT210-8K triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT210-8K embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package TO-252 is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	10/10/10	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
RMS on-state current ($T_c = 107^\circ C$)	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	25	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		27.5	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	3.125	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4.5	kV
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(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				35	
I_H	$I_T=100mA$		MAX.	15	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	900	V/ μs
(dI/dt) _c	(dV/dt) _c =10V/ μs , $T_j=125$		MIN.	3	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5	μs
t_{off}				25	
V_{CL}	$I_{CL}=0.1mA$ $t_p=1ms$		MIN.	850	V

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=3A$ $t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.79	V
R_D	Dynamic resistance	$T_j=125$	242	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.2	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	6.5	W
$R_{th(j-a)}$	junction to ambient (AC)	145	W

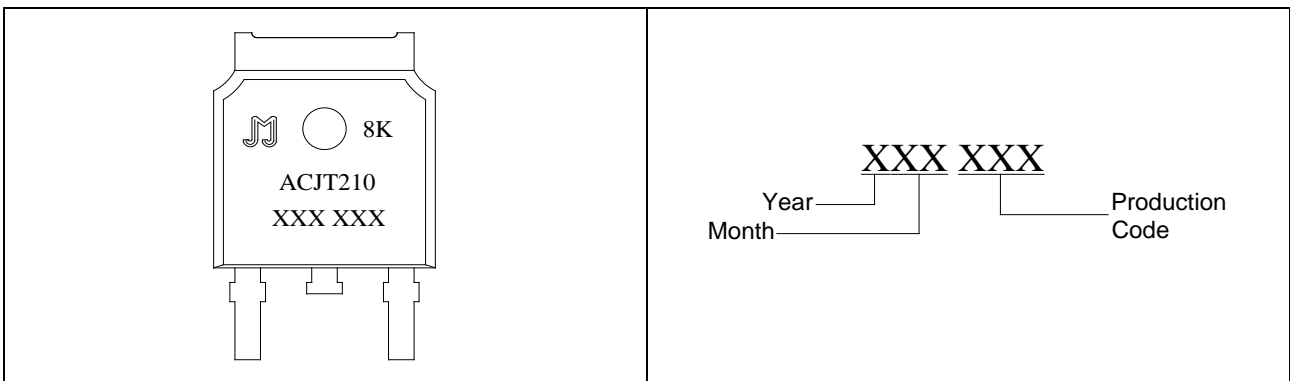
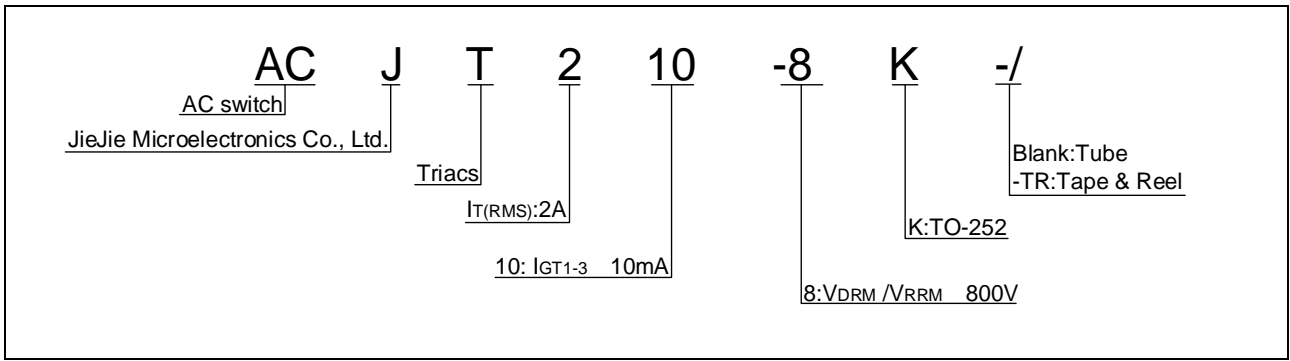


FIG.1 Maximum power dissipation versus RMS on-state current

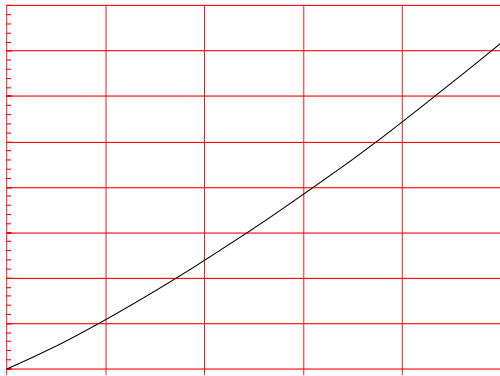


FIG.2: RMS on-state current versus case temperature

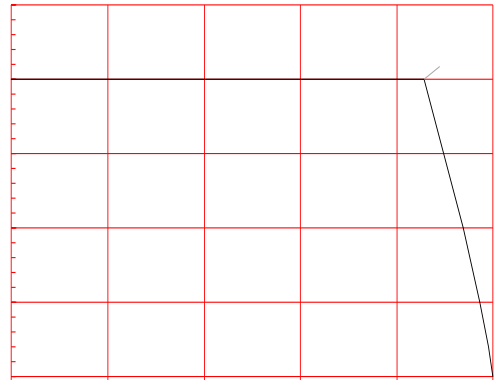


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

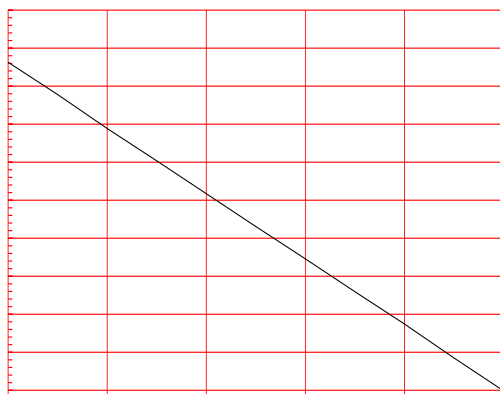
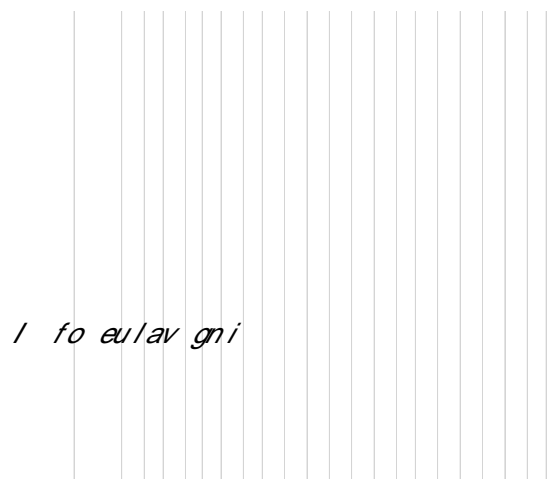


FIG.4: Surge peak on-state current versus number of cycles



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FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

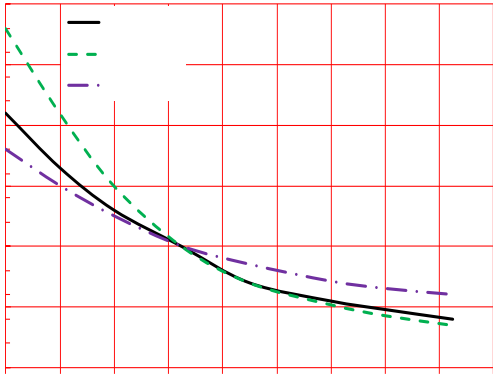
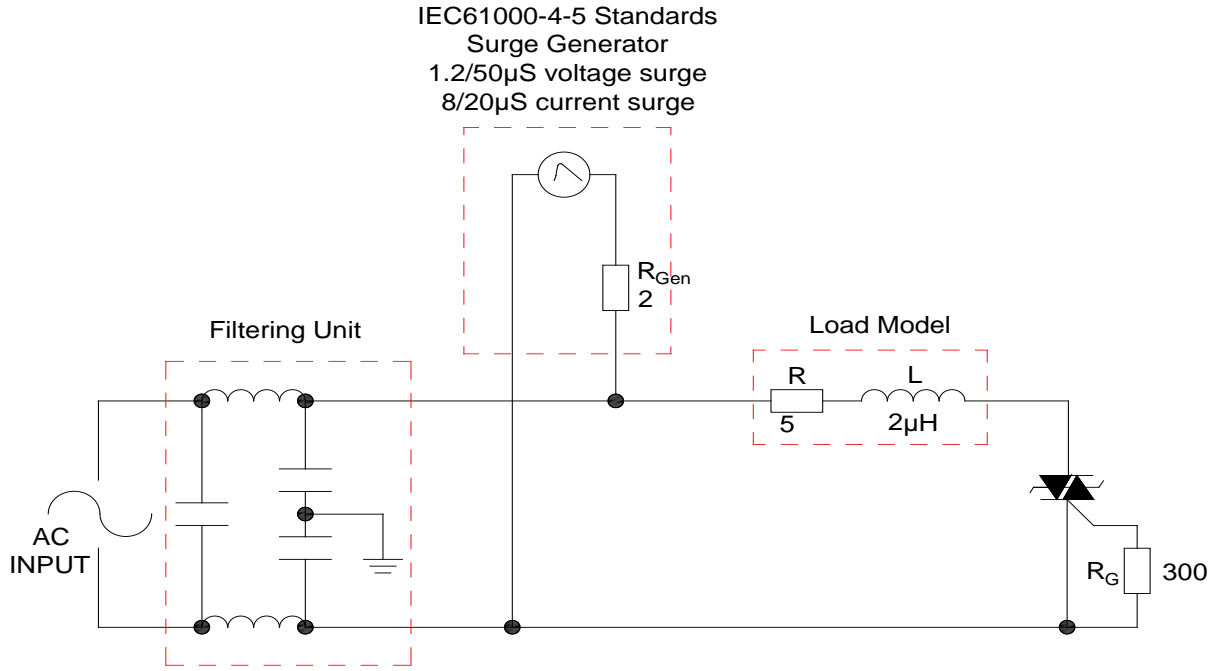
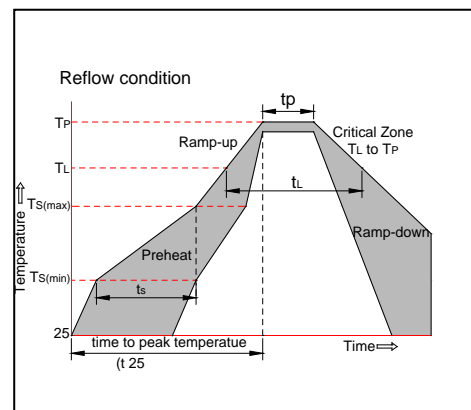


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

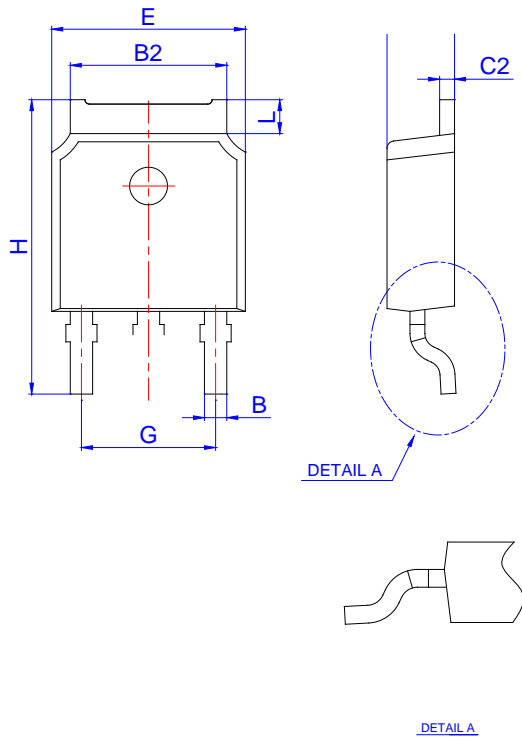


Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150
	-Temperature Max($T_{s(max)}$)	+200
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3 /sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 /sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)
Time within 5 of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 /sec. Max
Time 25 to Peak Temp (T_p)		8 min. Max
Do not exceed		+260



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
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ACCT210-8K-2,



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1						
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

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